

N-channel 100 V, 0.0036 Ω typ., 110 A, STripFET™ VII DeepGATE™ Power MOSFETs in I²PAK and TO-220 packages

Datasheet – production data

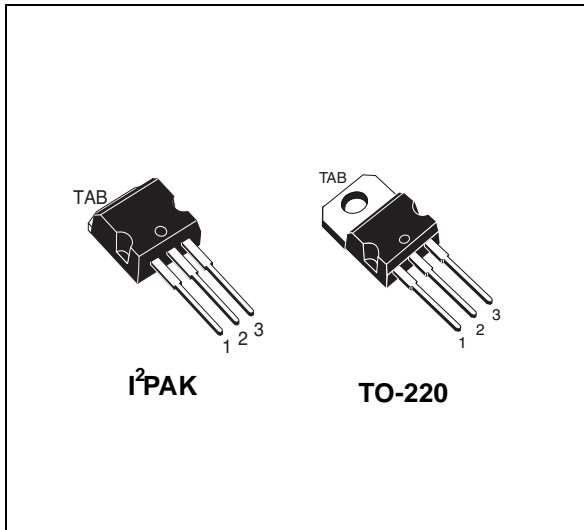
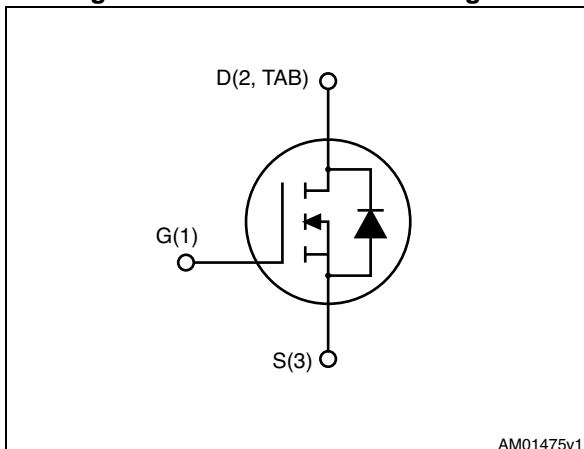


Figure 1. Internal schematic diagram



Features

Order codes	V _{DS}	R _{DS(on)max}	I _D	P _{TOT}
STI150N10F7	100 V	0.0042 Ω	110 A	250 W
STP150N10F7				

- 100% avalanche tested
- Ultra low on-resistance

Applications

- Switching applications

Description

These devices utilize the 7th generation of design rules of ST's proprietary STripFET™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STI150N10F7	150N10F7	I ² PAK	Tube
STP150N10F7		TO-220	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate- source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	110	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	110	A
$I_{DM}^{(1)}$	Drain current (pulsed)	440	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	250	W
T_J	Operating junction temperature	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature		$^\circ\text{C}$

1. Pulse width is limited by safe operating area

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.6	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 250\ \mu A$	100			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 100\ V$			1	μA
		$V_{GS} = 0, V_{DS} = 100\ V, T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0, V_{GS} = +20\ V$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu A$	2.5		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ V, I_D = 55\ A$		0.0036	0.0042	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\ V, f = 1\ MHz, V_{GS} = 0$	-	8115	-	pF
C_{oss}	Output capacitance		-	1510	-	pF
C_{riss}	Reverse transfer capacitance		-	67	-	pF
Q_g	Total gate charge	$V_{DD} = 50\ V, I_D = 110\ A, V_{GS} = 10\ V$ (see Figure 14)	-	117	-	nC
Q_{gs}	Gate-source charge		-	47	-	nC
Q_{gd}	Gate-drain charge		-	26	-	nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50\ V, I_D = 55\ A, R_G = 4.7\ \Omega, V_{GS} = 10\ V$ (see Figure 13)	-	33	-	ns
t_r	Rise time		-	57	-	ns
$t_{d(off)}$	Turn-off delay time		-	72	-	ns
t_f	Fall time		-	33	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		110	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		440	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 110 \text{ A}$, $V_{GS} = 0$	-		1.2	V
t_{rr}	Reverse recovery time	$I_{SD} = 110 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 80 \text{ V}$, $T_J = 150 \text{ }^\circ\text{C}$ (see Figure 15)	-	70		ns
Q_{rr}	Reverse recovery charge		-	165		nC
I_{RRM}	Reverse recovery current		-	4.7		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

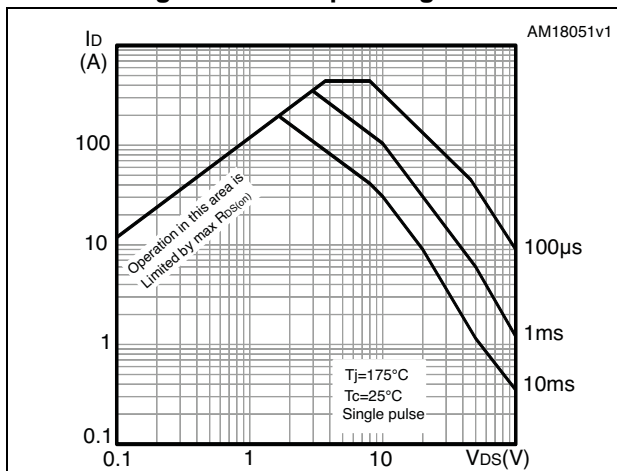


Figure 3. Thermal impedance

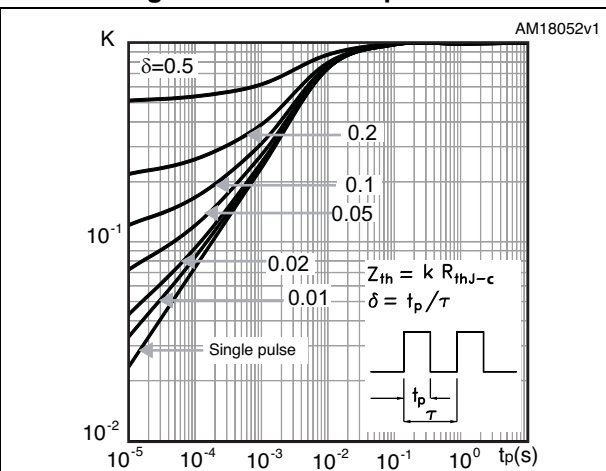


Figure 4. Output characteristics

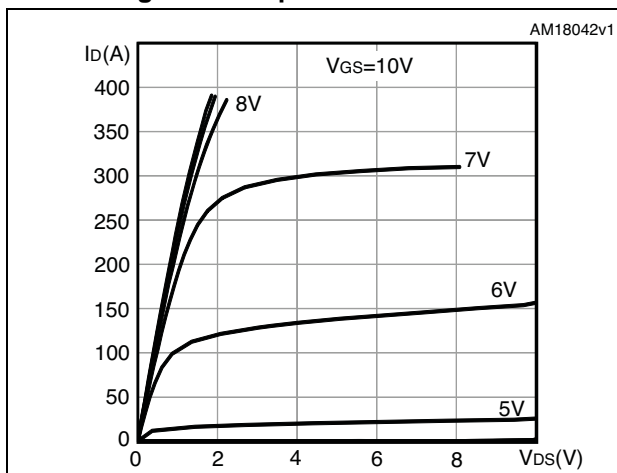


Figure 5. Transfer characteristics

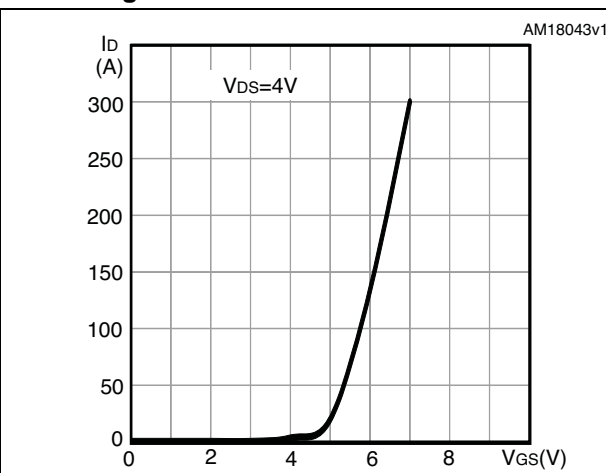


Figure 6. Gate charge vs gate-source voltage

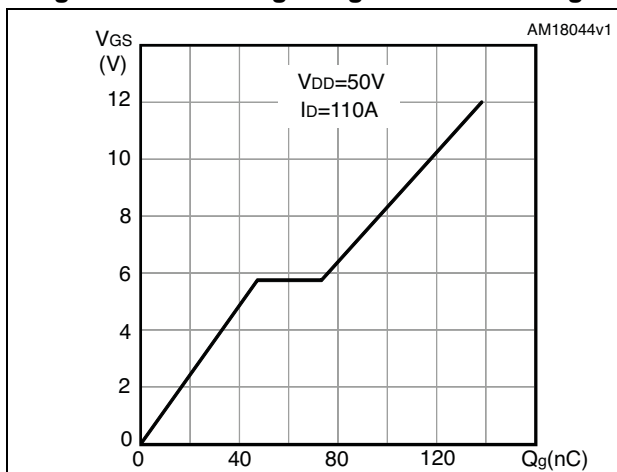


Figure 7. Static drain-source on-resistance

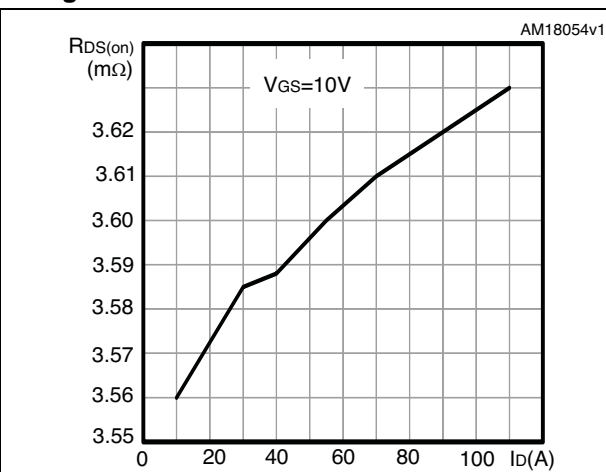


Figure 8. Capacitance variations

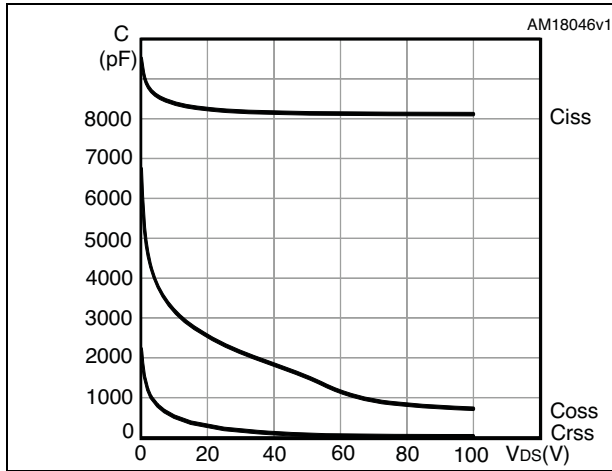


Figure 9. Normalized gate threshold voltage vs temperature

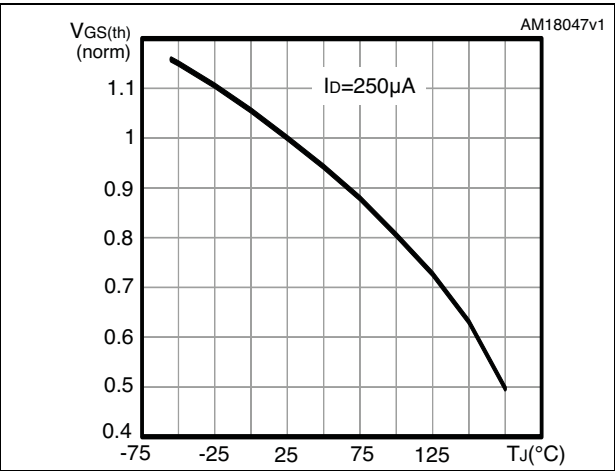


Figure 10. Normalized on-resistance vs temperature

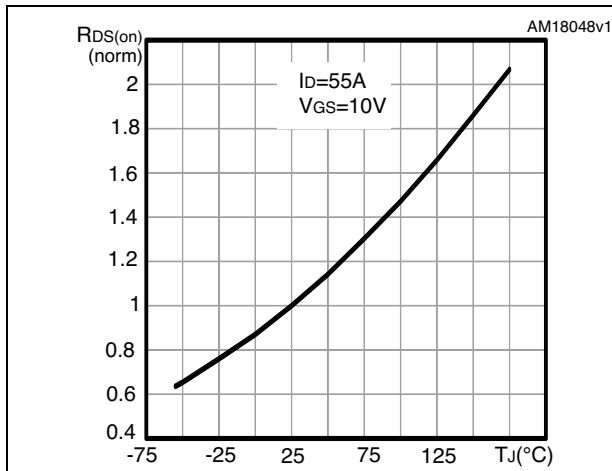


Figure 11. Normalized V(BR)DSS vs temperature

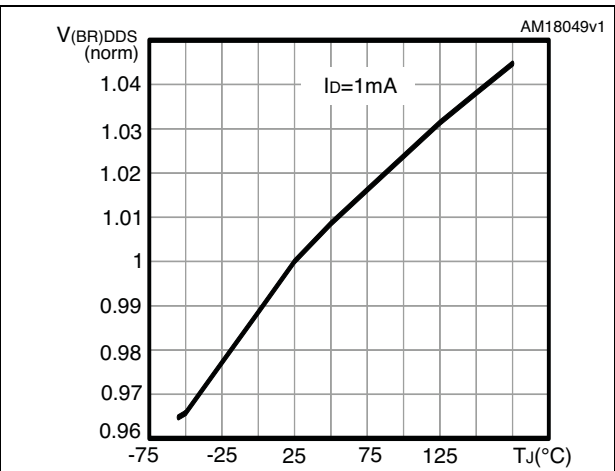
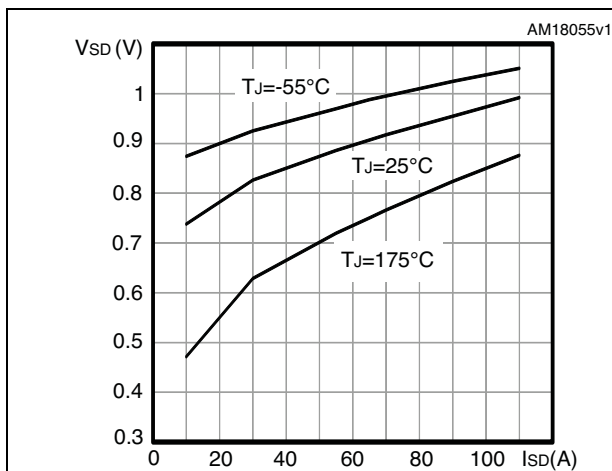
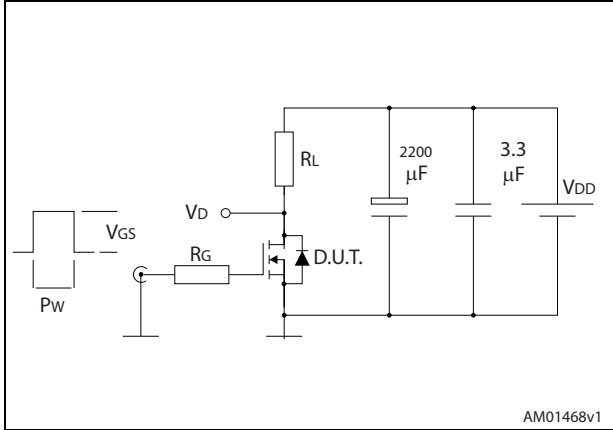


Figure 12. Source-drain diode forward characteristics



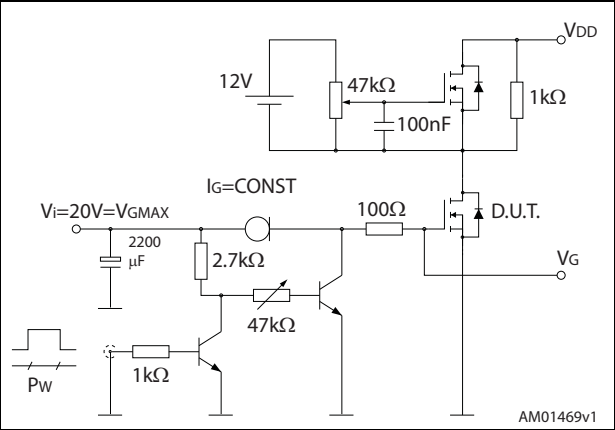
3 Test circuits

Figure 13. Switching times test circuit for resistive load



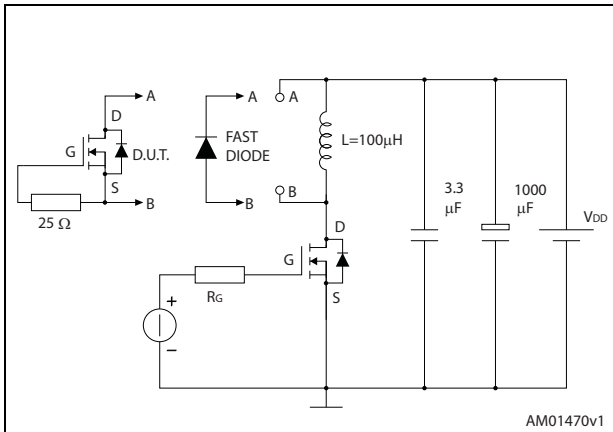
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Figure 14. Gate charge test circuit



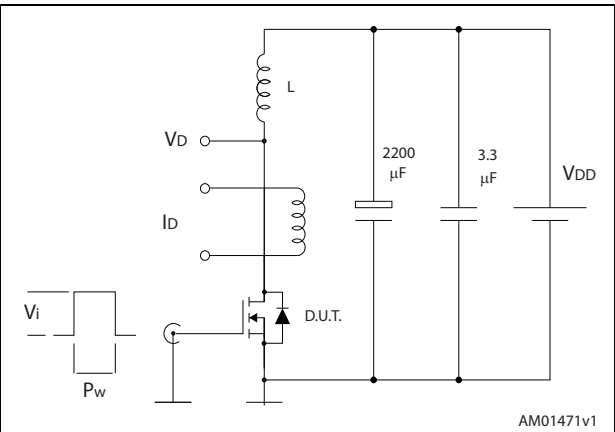
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Figure 15. Test circuit for inductive load switching and diode recovery times



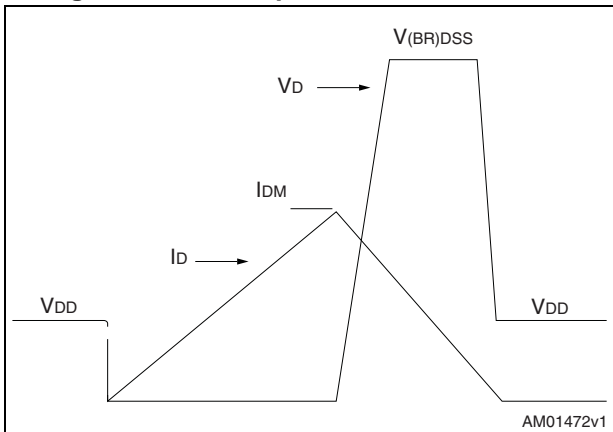
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Figure 16. Unclamped inductive load test circuit



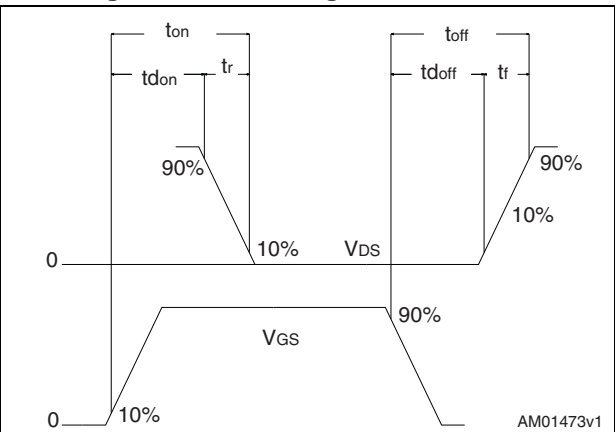
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Figure 17. Unclamped inductive waveform



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Figure 18. Switching time waveform

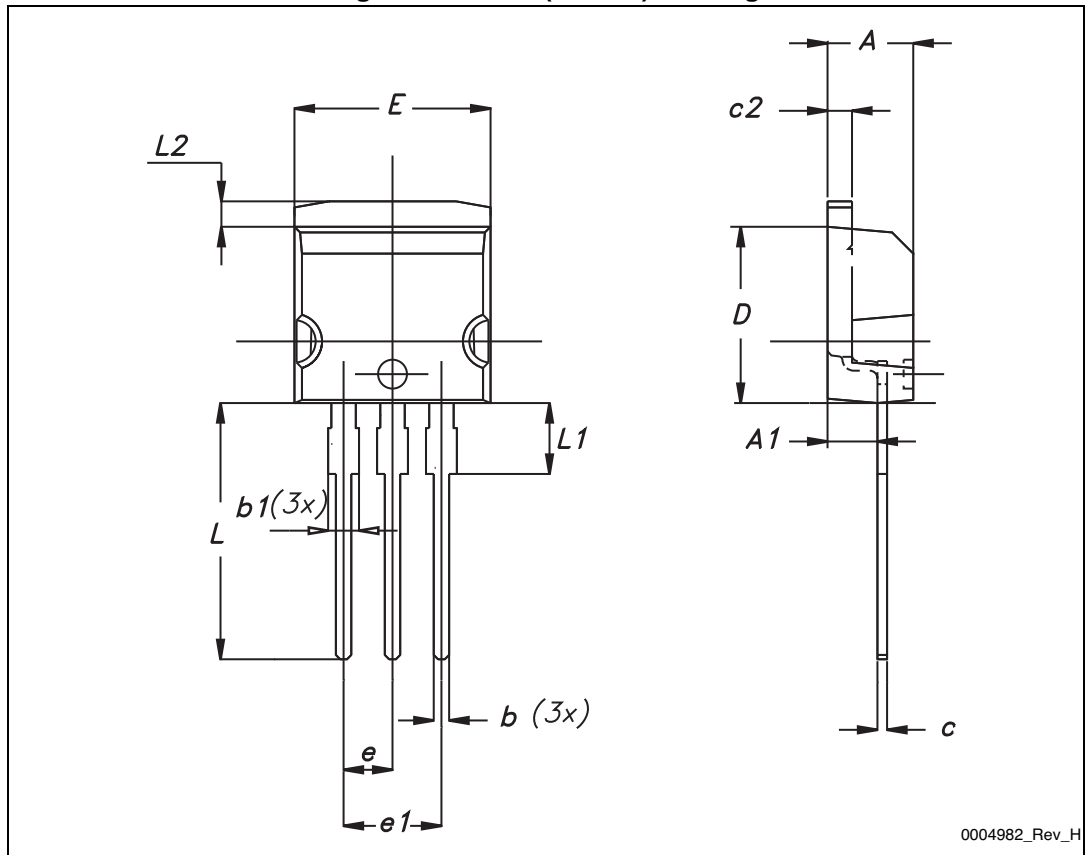


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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 19. I²PAK (TO-262) drawing



0004982_Rev_H

Table 8. I²PAK (TO-262) mechanical data

DIM.	mm.		
	min.	typ	max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

Figure 20. TO-220 type A drawing

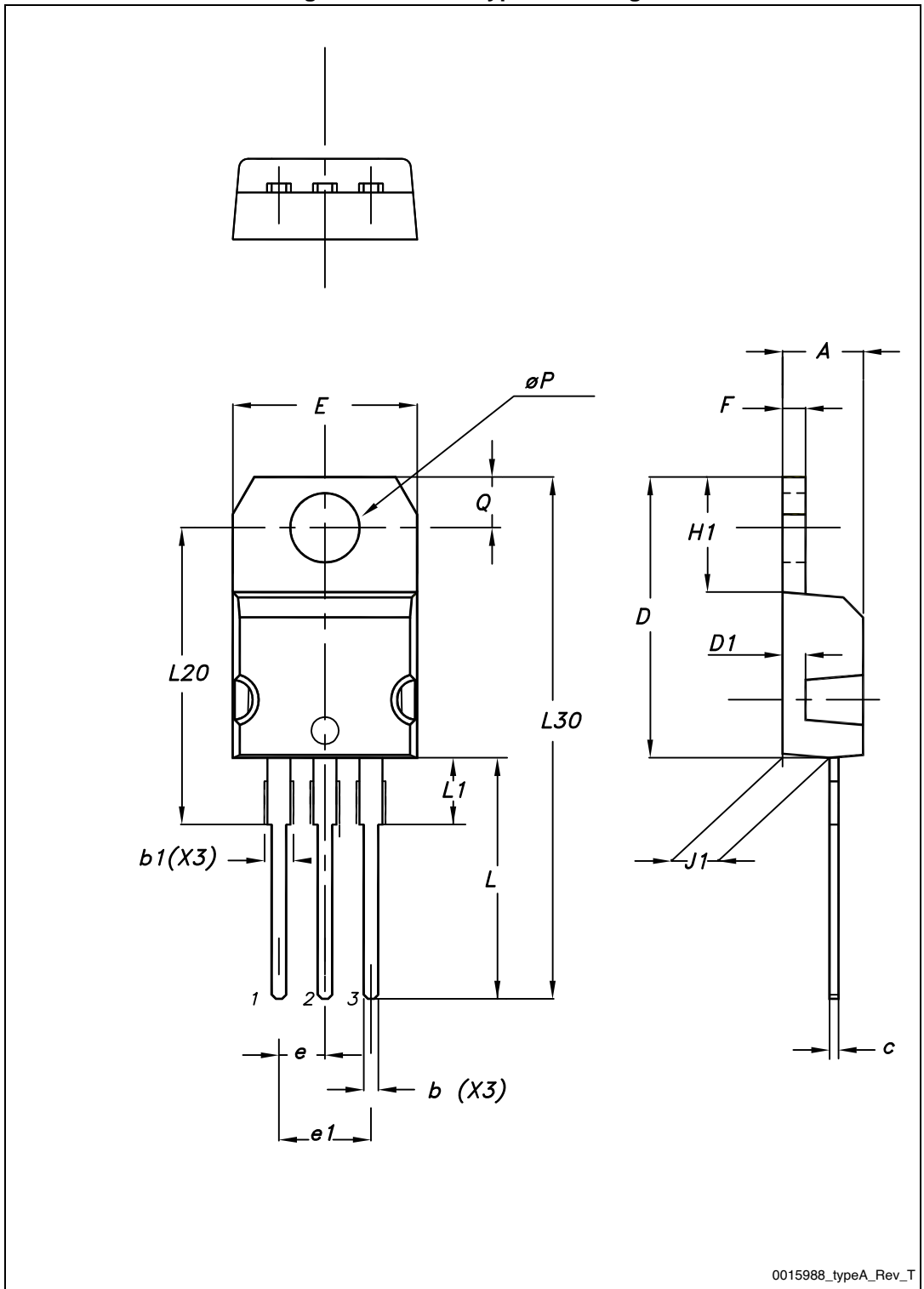


Table 9. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

5 Revision history

Table 10. Document revision history

Date	Revision	Changes
16-Apr-2013	1	First release.
22-Jan-2014	2	<ul style="list-style-type: none"> – The part number STH150N10F7-2 has been moved to a separate datasheet – Added: I²PAK package – Modified: Figure 1 – Modified: I_D and I_{DM} values in Table 2 – Modified: R_{thj-case} value in Table 3 – Modified: R_{DS(on)} values in Table 4 – Modified: V_{SD}, I_D and the entire typical values in Table 5, 6 and 7 – Updated: Figure 13, 14, 15 and 16 – Updated: Section 4: Package mechanical data – Added: Section 2.1: Electrical characteristics (curves) – Minor text changes
24-Feb-2014	3	<ul style="list-style-type: none"> – Datasheet status promoted from preliminary data to production data – Modified: Figure 10 – Minor text changes

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